



TURBO 2 ULTRAFAST HIGH VOLTAGE RECTIFIER

Table 1: Main Product Characteristics

$I_{F(AV)}$	Up to 2 x 40 A
V_{RRM}	600 V
T_j	175°C
V_F (typ)	1.0 V
t_{rr} (max)	65 ns

FEATURES AND BENEFITS

- Ultrafast switching
- Low reverse current
- Low thermal resistance
- Reduces switching & conduction losses

DESCRIPTION

The STTH60L06, which is using ST Turbo 2 600V technology, is specially suited for use in switching power supplies, and industrial applications, as rectification and discontinuous mode PFC boost diode.

Table 2: Order Codes

Part Number	Marking
STTH60L06CW	STTH60L06CW

Table 3: Absolute Ratings (limiting values, per diode)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		600	V
$I_{F(RMS)}$	RMS forward voltage		60	A
$I_{F(AV)}$	Average forward current $\delta = 0.5$	$T_c = 125^\circ\text{C}$ Per diode	30	A
		$T_c = 110^\circ\text{C}$ Per device	60	
		$T_c = 100^\circ\text{C}$ Per diode	40	
		$T_c = 80^\circ\text{C}$ Per device	80	
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ms}$ sinusoidal	210	A
T_{stg}	Storage temperature range		-65 to + 175	°C
T_j	Maximum operating junction temperature		175	°C

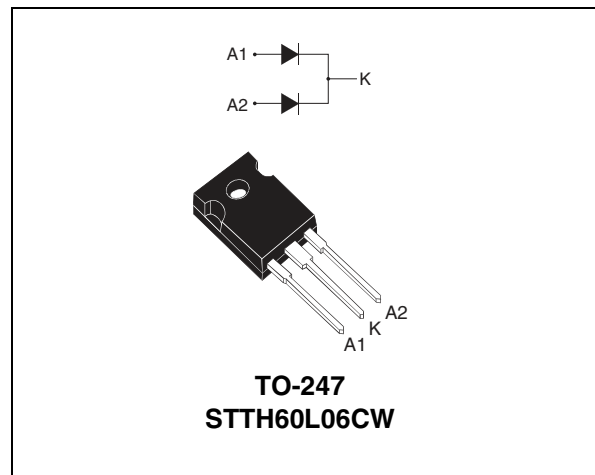


Table 4: Thermal Resistance

Symbol	Parameter		Value (max).	Unit
R _{th(j-c)}	Junction to case	Per diode	1.05	°C/W
		Total	0.68	
R _{th(c)}	Coupling		0.3	°C/W

When the diodes 1 and 2 are used simultaneously:
 $\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$

Table 5: Static Electrical Characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
I _R *	Reverse leakage current	T _j = 25°C	V _R = V _{RRM}			25	µA
		T _j = 150°C			80	800	
V _F **	Forward voltage drop	T _j = 25°C	I _F = 30A			1.55	V
		T _j = 150°C			1.0	1.25	
		T _j = 25°C	I _F = 60A			1.78	
		T _j = 150°C			1.24	1.55	

Pulse test: * tp = 5 ms, δ < 2%
 ** tp = 380 µs, δ < 2%

To evaluate the conduction losses use the following equation: $P = 0.95 \times I_{F(AV)} + 0.010 I_F^2(\text{RMS})$

Table 6: Dynamic Characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
t _{rr}	Reverse recovery time	T _j = 25°C	I _F = 0.5A I _{rr} = 0.25A I _R = 1A			65	ns
			I _F = 1A dI _F /dt = 50 A/µs V _R = 30V		65	90	
I _{RM}	Reverse recovery current	T _j = 125°C	I _F = 30A V _R = 400V dI _F /dt = 100 A/µs		11.5	16	A
t _{fr}	Forward recovery time	T _j = 25°C	I _F = 30A dI _F /dt = 100 A/µs V _{FR} = 1.1 x V _{Fmax}			500	ns
V _{FP}	Forward recovery voltage	T _j = 25°C	I _F = 30A dI _F /dt = 100 A/µs V _{FR} = 1.1 x V _{Fmax}		2.5		V

Figure 1: Conduction losses versus average forward current (per diode)

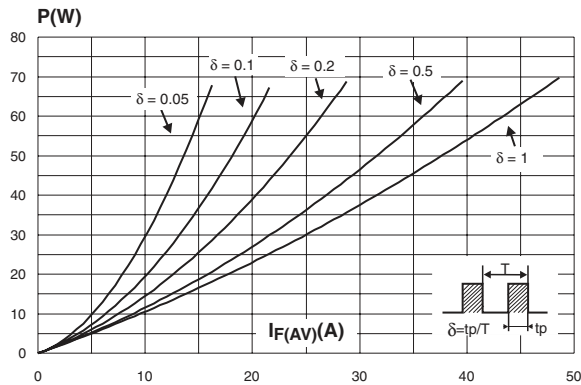


Figure 2: Forward voltage drop versus forward current (per diode)

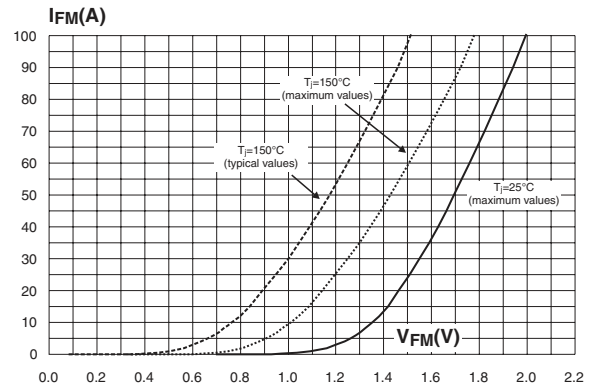


Figure 3: Relative variation of thermal impedance junction to case versus pulse duration

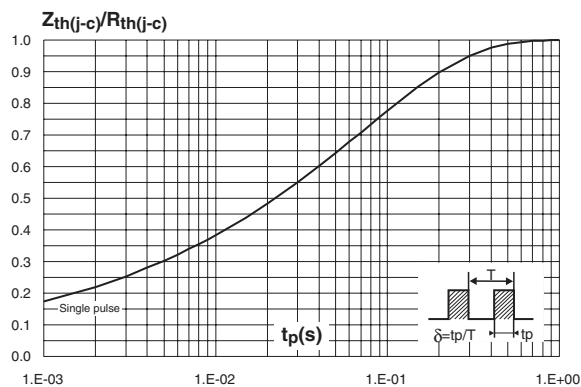


Figure 4: Peak reverse recovery current versus di_F/dt (typical values, per diode)

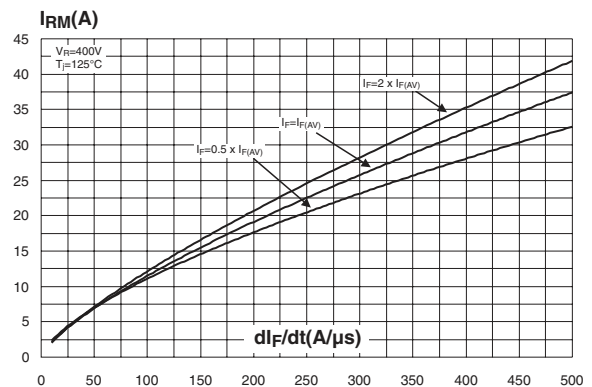


Figure 5: Reverse recovery time versus di_F/dt (typical values, per diode)

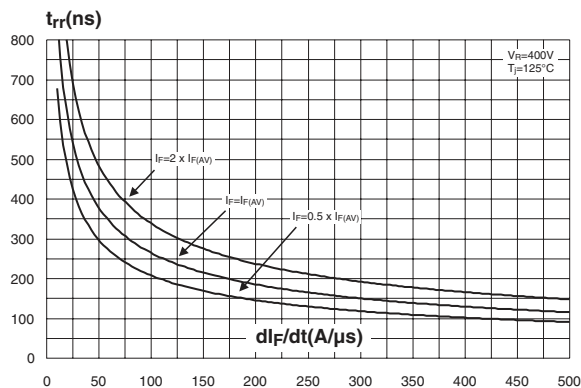


Figure 6: Reverse recovery charges versus di_F/dt (typical values, per diode)

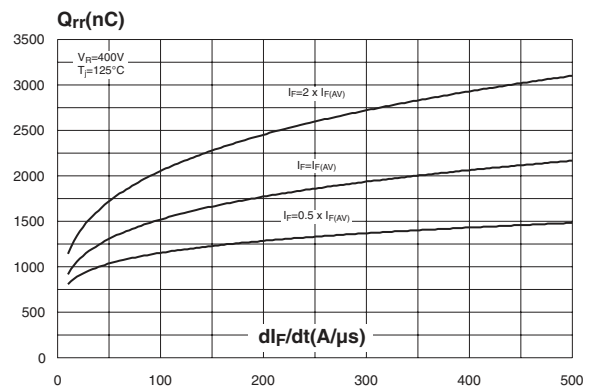


Figure 7: Reverse recovery softness factor versus di_F/dt (typical values, per diode)

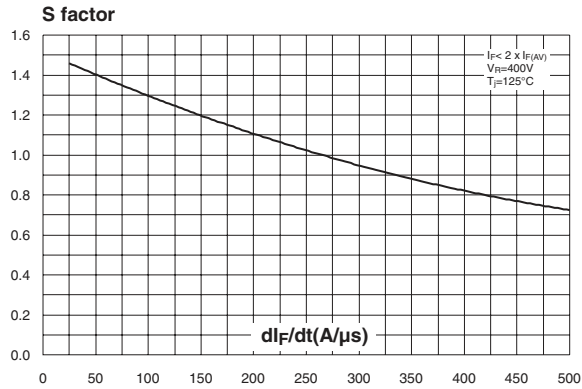


Figure 8: Relative variations of dynamic parameters versus junction temperature

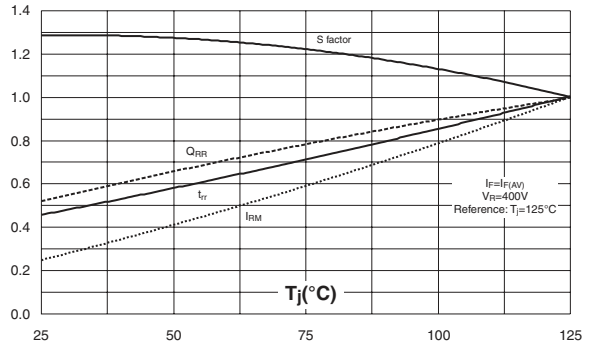


Figure 9: Transient peak forward voltage versus di_F/dt (typical values, per diode)

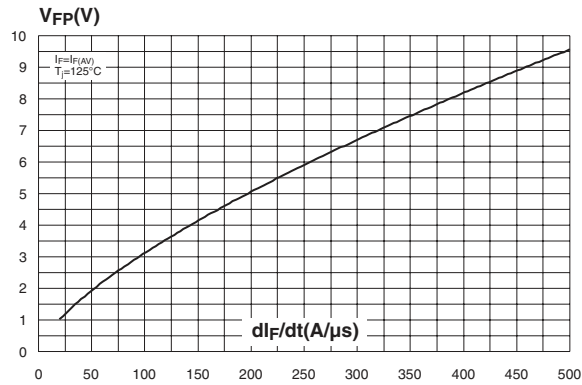


Figure 10: Forward recovery time versus di_F/dt (typical values, per diode)

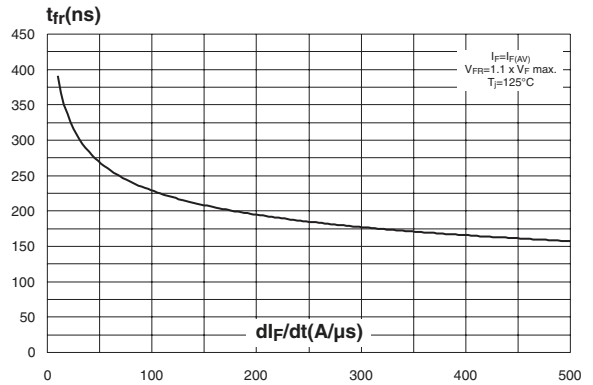


Figure 11: Junction capacitance versus reverse voltage applied (typical values, per diode)

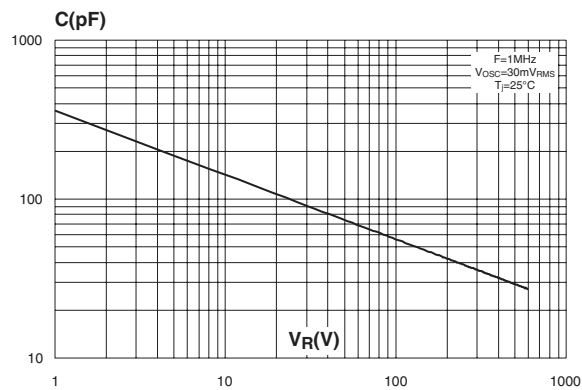


Figure 12: TO-247 Package Mechanical Data

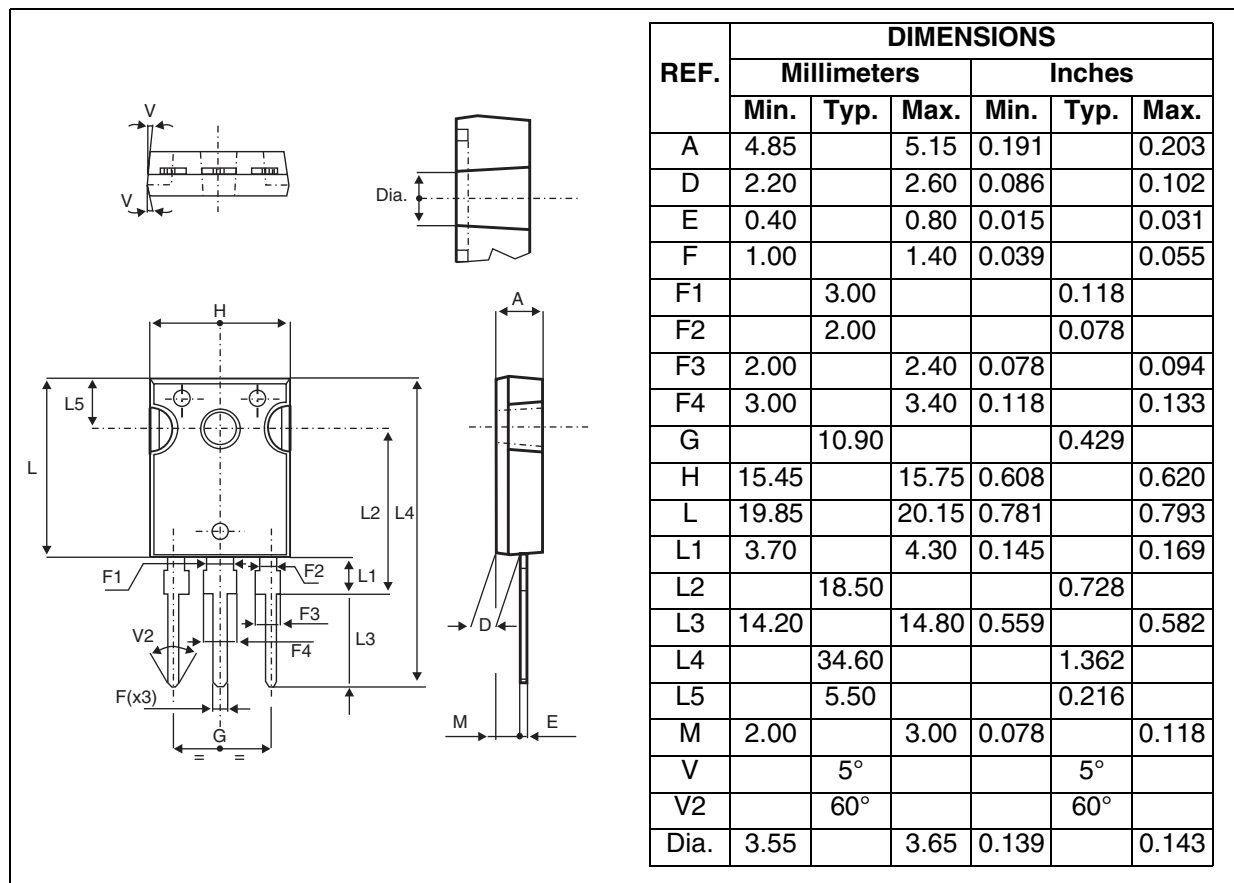


Table 7: Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTH60L06CW	STTH60L06CW	TO-247	4.46 g	50	Tube

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.8 m.N.
- Maximum torque value: 1.0 m.N.

Table 8: Revision History

Date	Revision	Description of Changes
07-Sep-2004	1	First issue

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